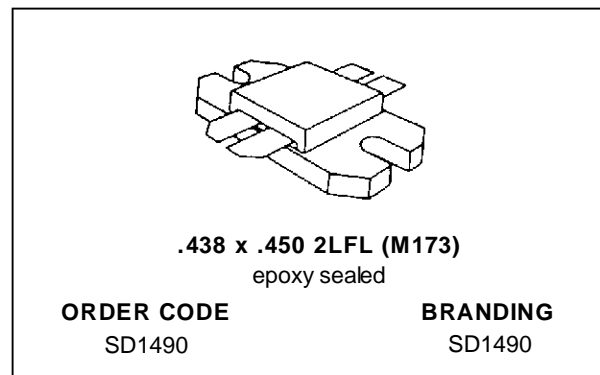
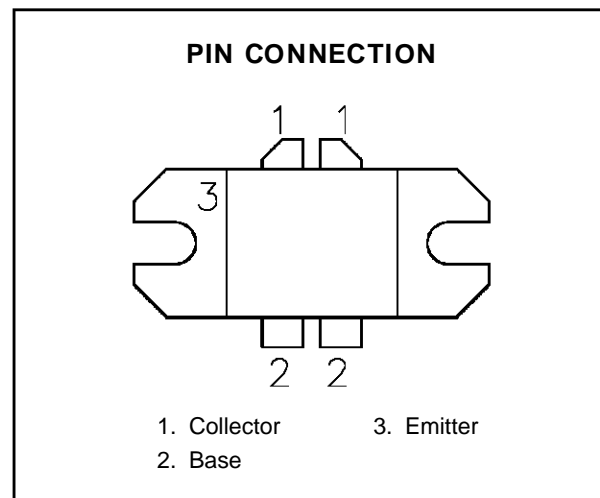


**RF & MICROWAVE TRANSISTORS
TV/LINEAR APPLICATIONS**

- 470 - 860 MHz
- 28 VOLTS
- CLASS A PUSH PULL
- DESIGNED FOR HIGH POWER LINEAR OPERATION
- HIGH SATURATED POWER CAPABILITY
- GOLD METALLIZATION
- DIFFUSED EMITTER BALLAST RESISTORS
- COMMON EMITTER CONFIGURATION
- INTERNAL INPUT MATCHING
- $P_{OUT} = 25 \text{ W MIN. WITH } 9.0 \text{ dB GAIN}$


DESCRIPTION

The SD1490 is a gold metallized epitaxial silicon NPN planar transistor using diffused emitter ballast resistors for high linearity Class A operation in UHF and Band IV, V television transmitters and transposers.


ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}\text{C}$)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	45	V
V_{CEO}	Collector-Emitter Voltage	30	V
V_{EBO}	Emitter-Base Voltage	3.0	V
I_C	Device Current	8	A
P_{DISS}	Power Dissipation	135	W
T_J	Junction Temperature	+200	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	- 50 to +150	$^{\circ}\text{C}$

THERMAL DATA

$R_{TH(j-c)}$	Junction-Case Thermal Resistance	1.3	$^{\circ}\text{C/W}$
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SD1490

ELECTRICAL SPECIFICATIONS ($T_{\text{case}} = 25^{\circ}\text{C}$)

STATIC

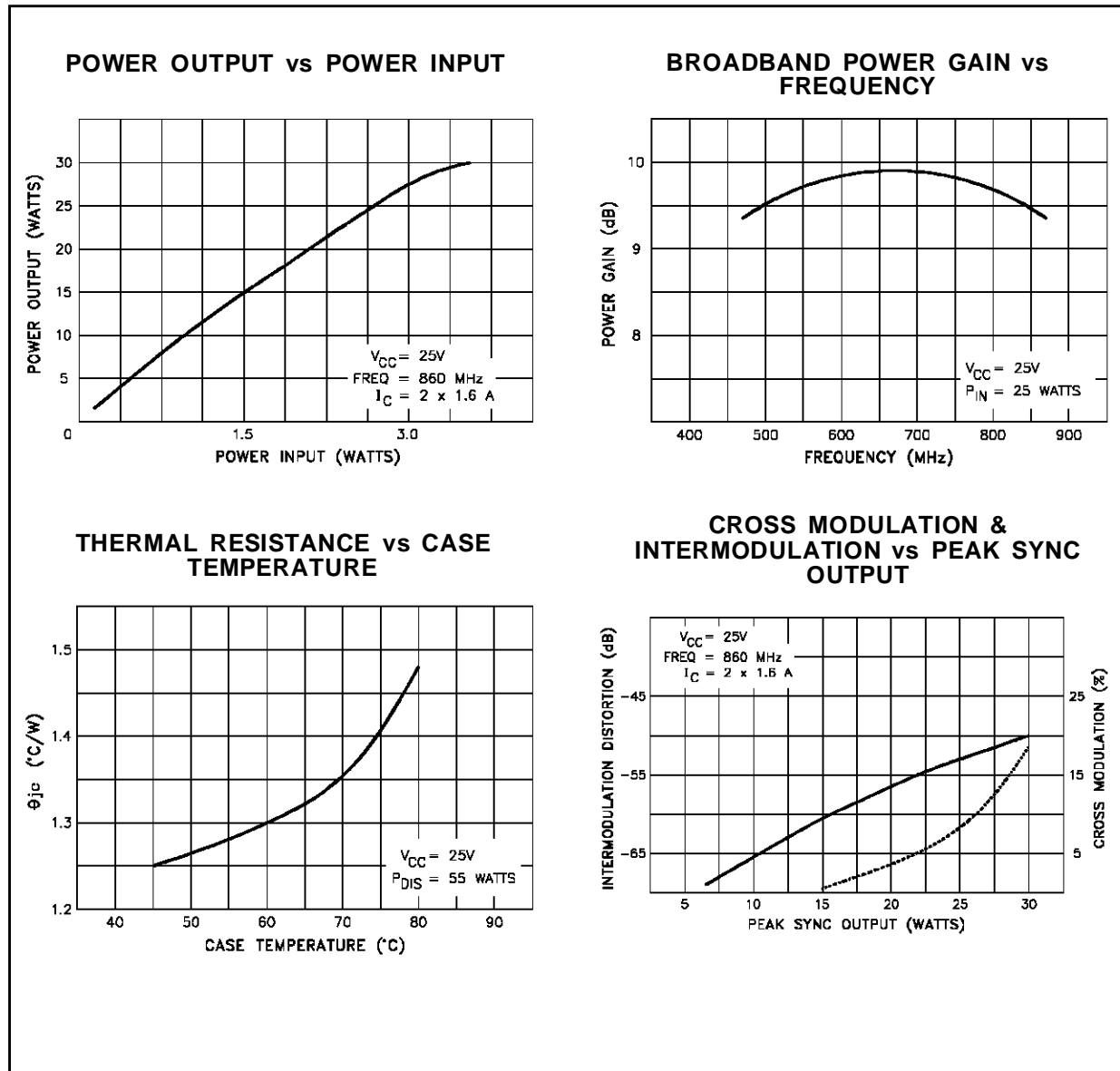
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV_{CBO}	$I_{\text{C}} = 50\text{mA}$	$I_{\text{E}} = 0\text{mA}$	45	—	—	V
BV_{CEO}	$I_{\text{C}} = 200\text{mA}$	$I_{\text{B}} = 0\text{mA}$	30	—	—	V
BV_{EBO}	$I_{\text{E}} = 10\text{mA}$	$I_{\text{C}} = 0\text{mA}$	3.0	—	—	V
I_{CEO}	$V_{\text{CE}} = 25\text{V}$	$I_{\text{E}} = 0\text{mA}$	—	—	5	mA
h_{FE}	$V_{\text{CE}} = 5\text{V}$	$I_{\text{C}} = 3\text{A}$	10	—	80	—

DYNAMIC

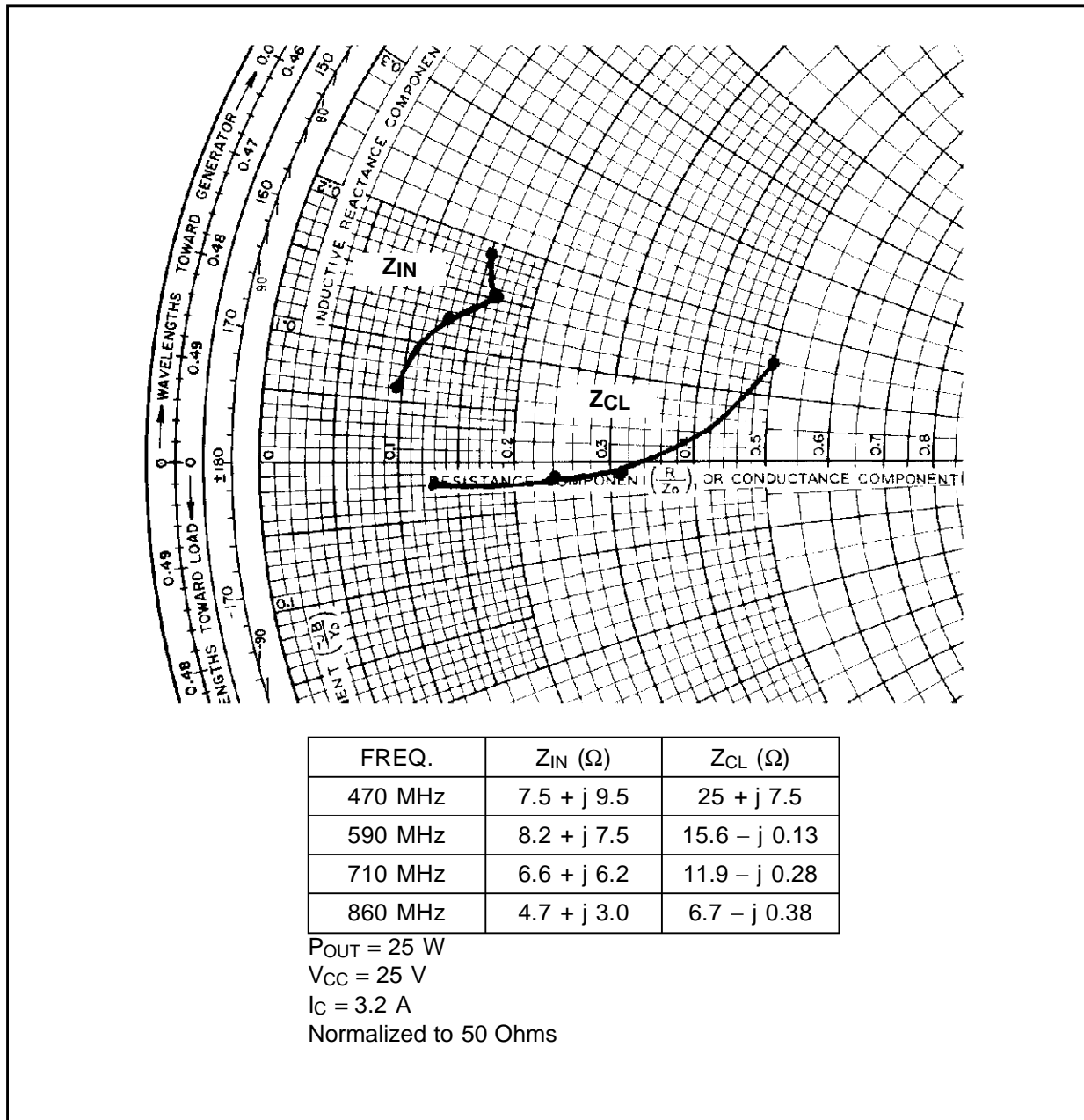
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P_{OUT}	$f = 860\text{ MHz}$	$V_{\text{CE}} = 25\text{ V}$	$I_{\text{C}} = 3.2\text{ A}$	25	—	—	W
G_{P}	$f = 860\text{ MHz}$	$V_{\text{CE}} = 25\text{ V}$	$I_{\text{C}} = 3.2\text{ A}$	8.0	—	—	dB
CMOD	$f = 860\text{ MHz}$	$V_{\text{CE}} = 25\text{ V}$	$P_{\text{REF}} = 25\text{ W}$	—	—	20	%
IMD_3^*	$f = 860\text{ MHz}$	$V_{\text{CE}} = 25\text{ V}$	$P_{\text{REF}} = 25\text{ W}$	—	—	-45	dB
COB	$f = 1\text{ MHz}$	$V_{\text{CB}} = 28\text{ V}$		—	70	—	pF

Note: * 3 Tone Testing (- 8, - 10, - 16 dB Relative to P_{REF})

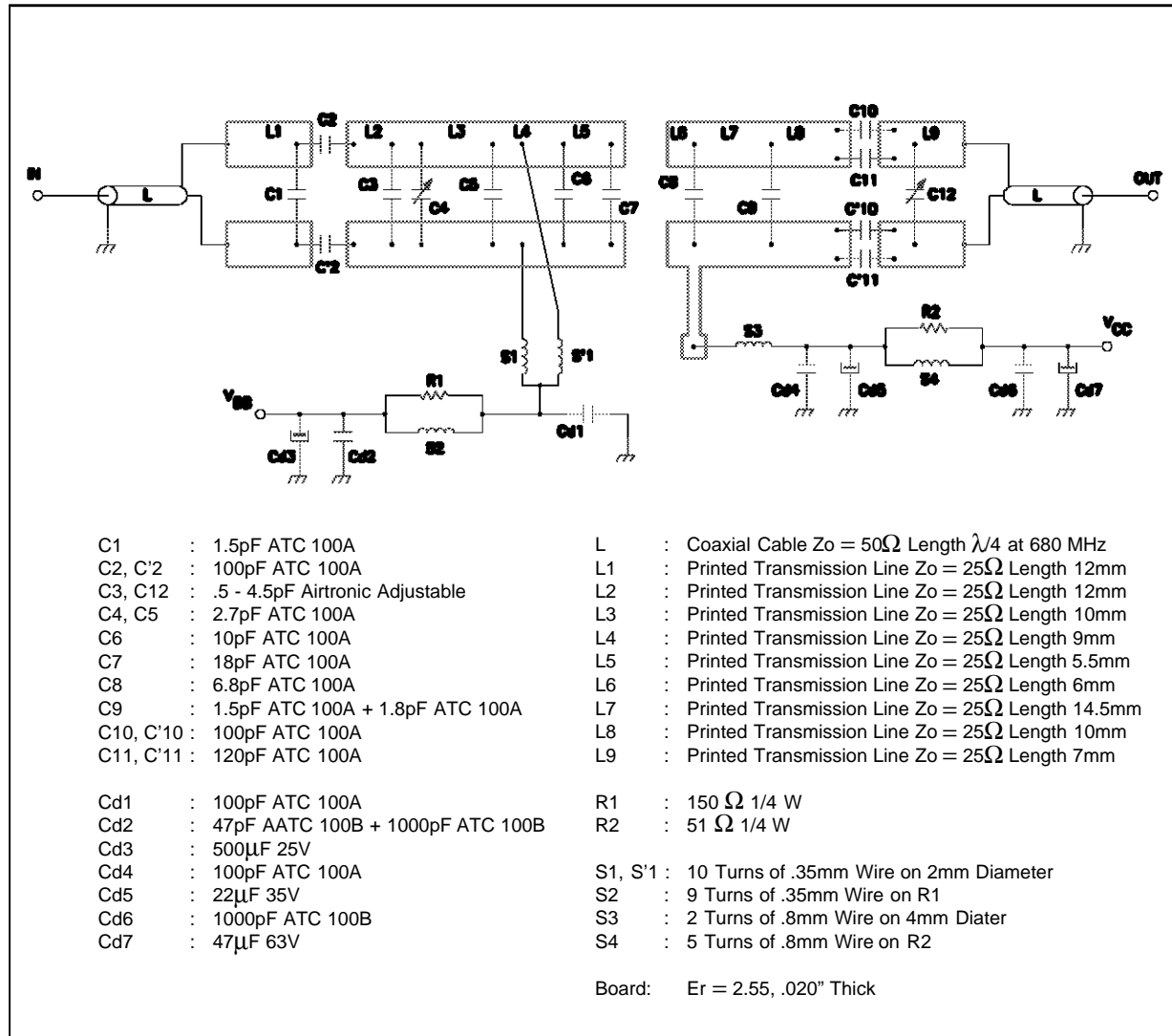
TYPICAL PERFORMANCE



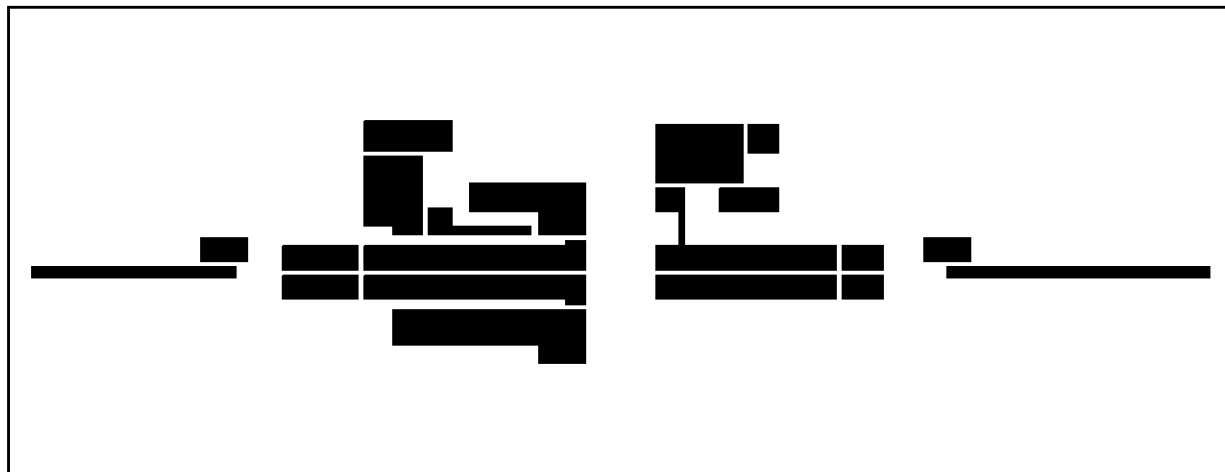
IMPEDANCE DATA



TEST CIRCUIT

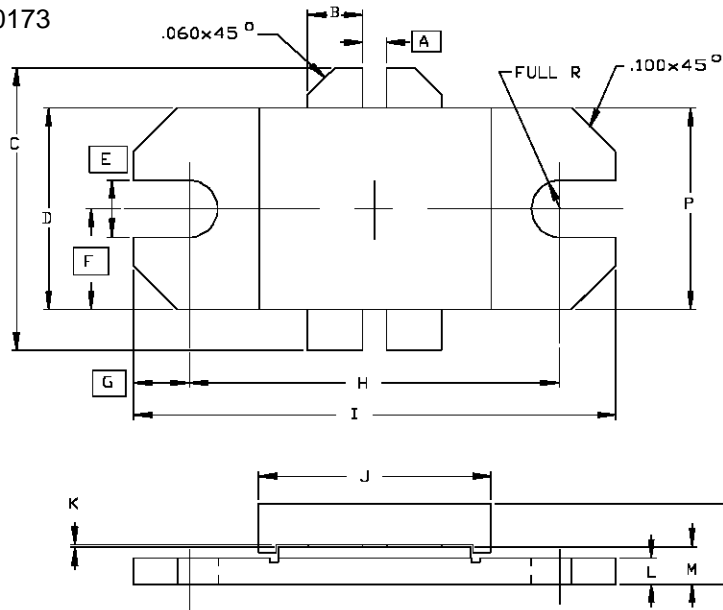


TEST CIRCUIT LAYOUT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.12-0173



SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.055/1,40		K	.002/0,05	.006/0,15
B	.120/3,05	.130/3,30	L	.055/1,40	.065/1,65
C		.785/19,94	M	.080/2,03	.095/2,41
D	.455/11,56	.465/11,81	N		.195/4,95
E	.125/3,18		P	.455/11,56	.465/11,81
F	.230/5,84				
G	.128/3,25				
H	.838/21,28	.850/21,59			
I	1.095/27,81	1.105/28,07			
J	.525/13,34	.535/13,59			

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